

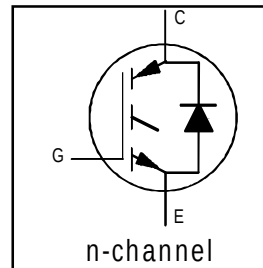
IRG4RC10SD

INSULATED GATE BIPOLAR TRANSISTOR WITH
ULTRAFAST SOFT RECOVERY DIODE

Standard Speed CoPack
IGBT

Features

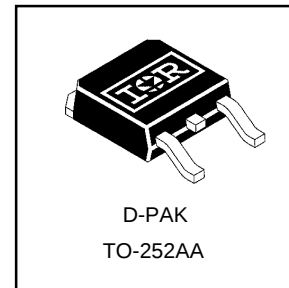
- Extremely low voltage drop 1.1V(typ) @ 2A
- S-Series: Minimizes power dissipation at up to 3 KHz PWM frequency in inverter drives, up to 4 KHz in brushless DC drives.
- Tight parameter distribution
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard TO-252AA package



$V_{CES} = 600V$
$V_{CE(on)} \text{ typ.} = 1.10V$
@ $V_{GE} = 15V, I_C = 2.0A$

Benefits

- Generation 4 IGBT's offer highest efficiencies available
- IGBT's optimized for specific application conditions
- HEXFRED diodes optimized for performance with IGBT's. Minimized recovery characteristics require less/no snubbing
- Lower losses than MOSFET's conduction and Diode losses



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	14	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	8.0	
I_{CM}	Pulsed Collector Current ①	18	
I_{LM}	Clamped Inductive Load Current ②	18	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	4.0	
I_{FM}	Diode Maximum Forward Current	16	V
V_{GE}	Gate-to-Emitter Voltage	± 20	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	38	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	15	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	3.3	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	—	7.0	
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)*	—	50	
Wt	Weight	0.3 (0.01)	—	g (oz)

* When mounted on 1" square PCB (FR-4 or G-10 Material).

For recommended footprint and soldering techniques refer to application note #AN-994

IRG4RC10SD

International
IR Rectifier

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage③	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.64	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.58	1.7	V	$I_C = 8.0A$
		—	2.05	—		$I_C = 14.0A$
		—	1.68	—		$I_C = 8.0A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-9.5	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance④	3.65	5.48	—	S	$V_{CE} = 100V, I_C = 8.0A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
V_{FM}	Diode Forward Voltage Drop	—	1.5	1.8	V	$I_C = 4.0A$
		—	1.4	1.7		$I_C = 4.0A, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	15	22	nC	$I_C = 8.0A$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	2.42	3.6		$V_{CC} = 400V$
Q_{gc}	Gate - Collector Charge (turn-on)	—	6.53	9.8		$V_{GE} = 15V$
$t_{d(on)}$	Turn-On Delay Time	—	76	—	ns	$T_J = 25^\circ\text{C}$
t_r	Rise Time	—	32	—		$I_C = 8.0A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	815	1200		$V_{GE} = 15V, R_G = 100\Omega$
t_f	Fall Time	—	720	1080		Energy losses include "tail" and diode reverse recovery.
E_{on}	Turn-On Switching Loss	—	0.31	—	mJ	See Fig. 9, 10, 18
E_{off}	Turn-Off Switching Loss	—	3.28	—		
E_{ts}	Total Switching Loss	—	3.60	10.9	mJ	
E_{ts}	Total Switching Loss	—	1.46	2.6		$I_C = 5.0A$
$t_{d(on)}$	Turn-On Delay Time	—	70	—	ns	$T_J = 150^\circ\text{C}$, See Fig. 10,11, 18
t_r	Rise Time	—	36	—		$I_C = 8.0A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	890	—		$V_{GE} = 15V, R_G = 100\Omega$
t_f	Fall Time	—	890	—		Energy losses include "tail" and diode reverse recovery.
E_{ts}	Total Switching Loss	—	3.83	—	mJ	
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	280	—	pF	$V_{GE} = 0V$
C_{oes}	Output Capacitance	—	30	—		$V_{CC} = 30V$
C_{res}	Reverse Transfer Capacitance	—	4.0	—		$f = 1.0MHz$
t_{rr}	Diode Reverse Recovery Time	—	28	42	ns	$T_J = 25^\circ\text{C}$ See Fig. 14
		—	38	57		$T_J = 125^\circ\text{C}$
I_{rr}	Diode Peak Reverse Recovery Current	—	2.9	5.2	A	$T_J = 25^\circ\text{C}$ See Fig. 15
		—	3.7	6.7		$T_J = 125^\circ\text{C}$
Q_{rr}	Diode Reverse Recovery Charge	—	40	60	nC	$T_J = 25^\circ\text{C}$ See Fig. 16
		—	70	105		$T_J = 125^\circ\text{C}$
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During t_b	—	280	—	A/ μs	$T_J = 25^\circ\text{C}$ See Fig. 17
		—	235	—		$T_J = 125^\circ\text{C}$

Details of note ① through ④ are on the last page

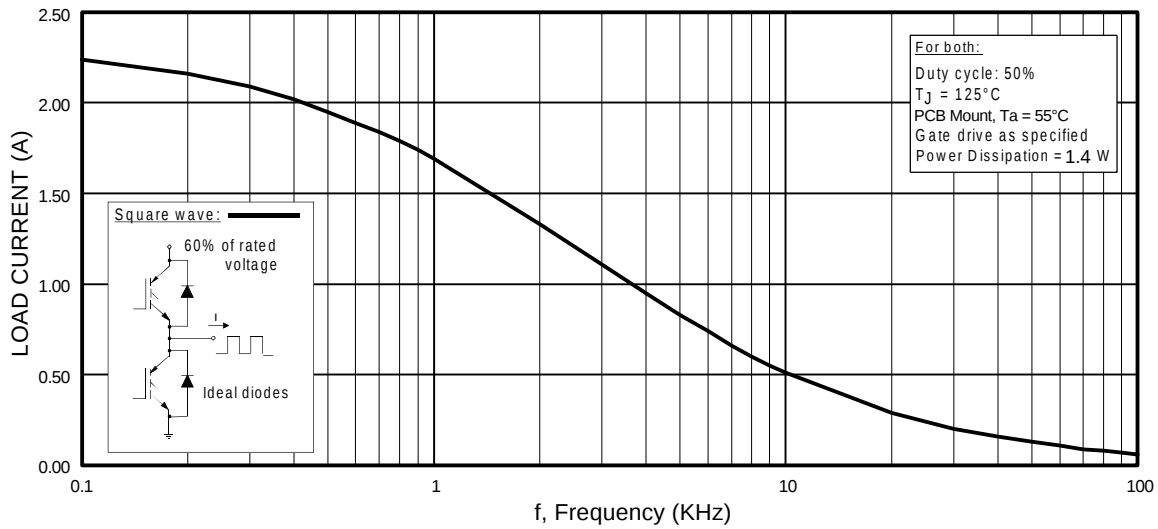


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

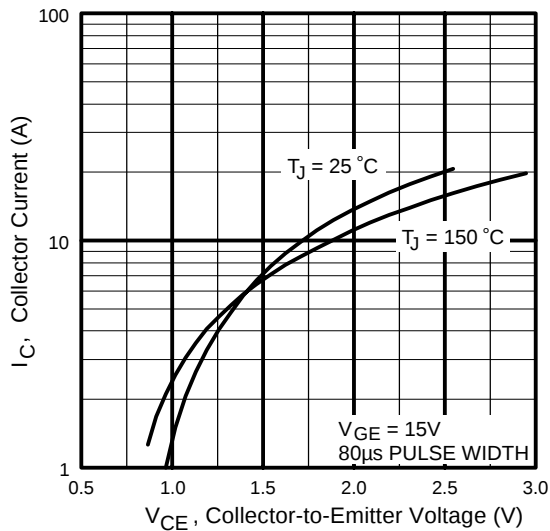


Fig. 2 - Typical Output Characteristics

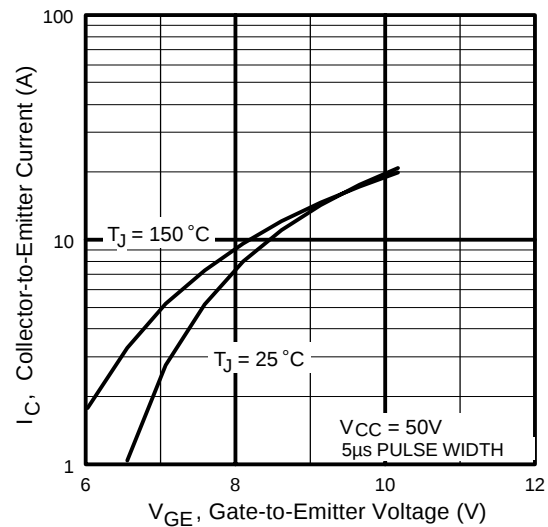


Fig. 3 - Typical Transfer Characteristics

IRG4RC10SD

International
IR Rectifier

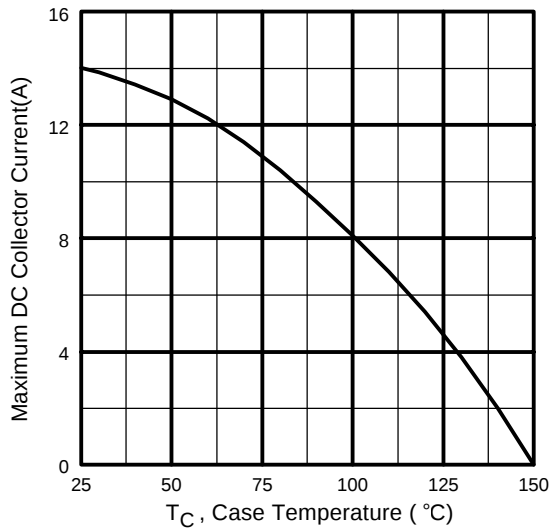


Fig. 4 - Maximum Collector Current vs. Case Temperature

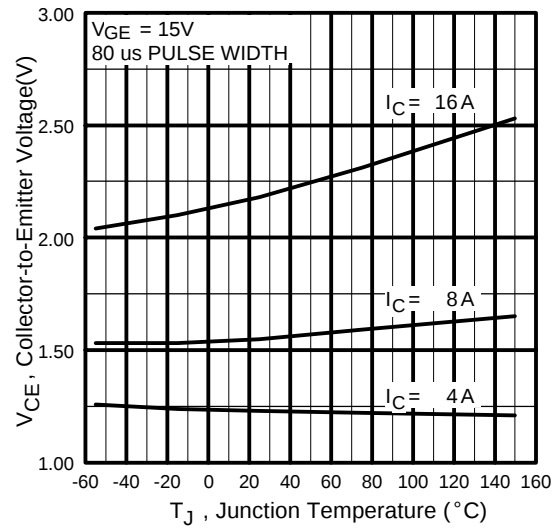


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

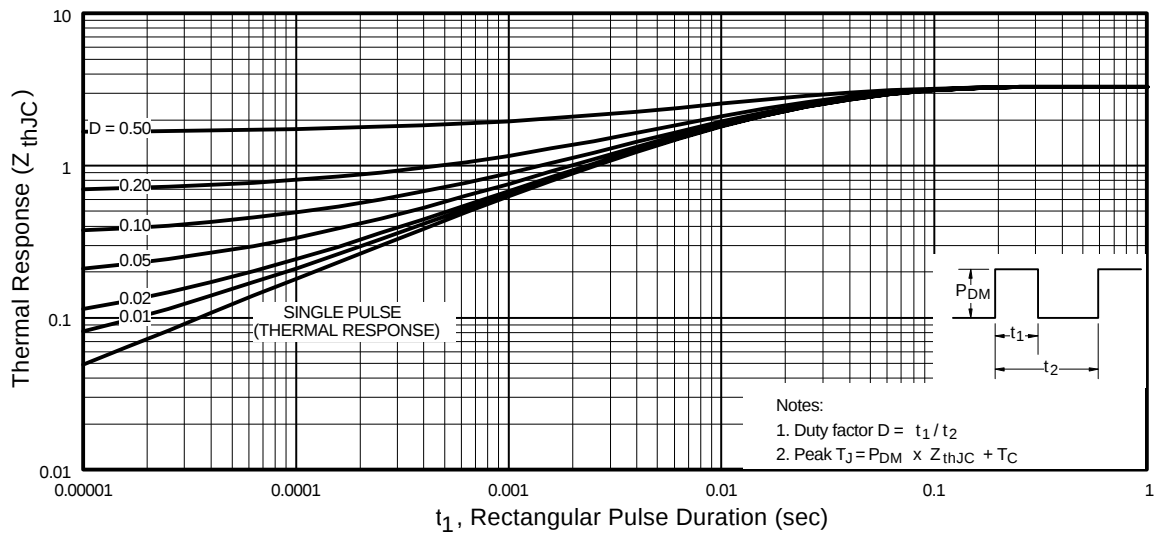


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

IRG4RC10SD

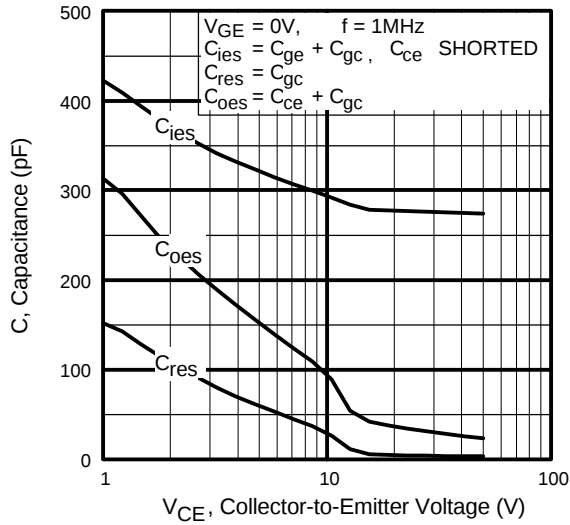


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

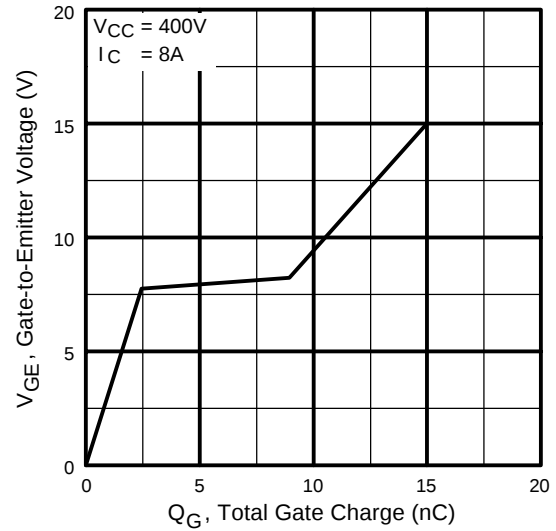


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

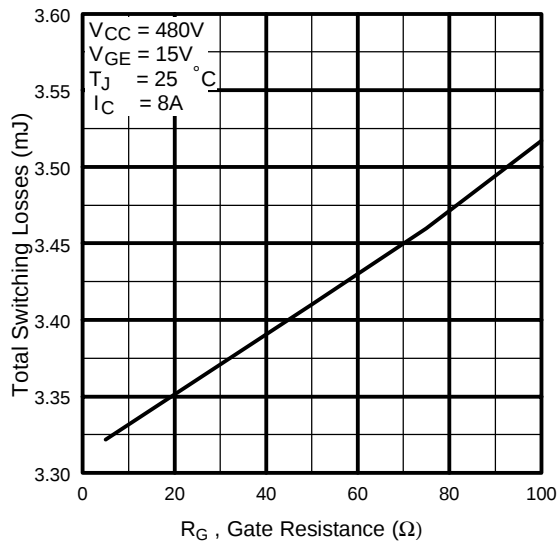


Fig. 9 - Typical Switching Losses vs. Gate Resistance

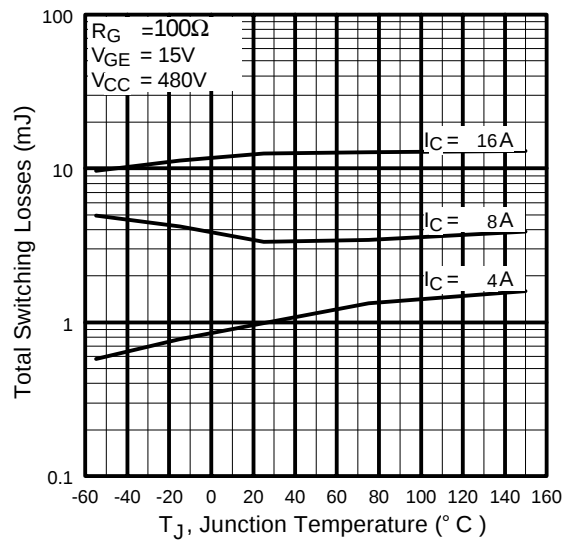


Fig. 10 - Typical Switching Losses vs. Junction Temperature

IRG4RC10SD

International
IR Rectifier

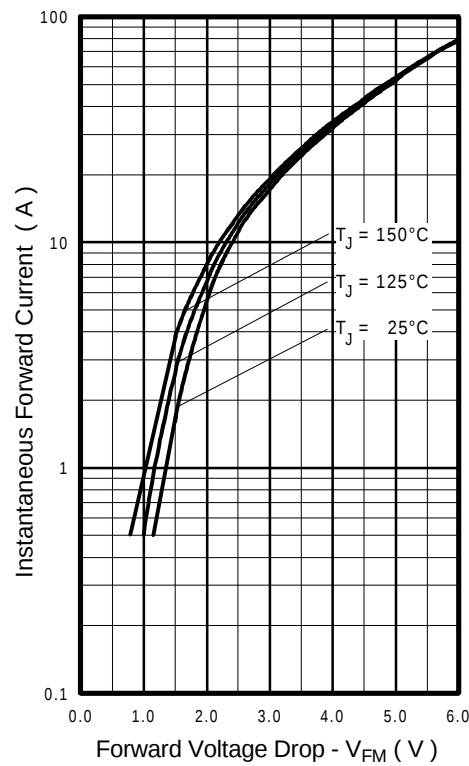
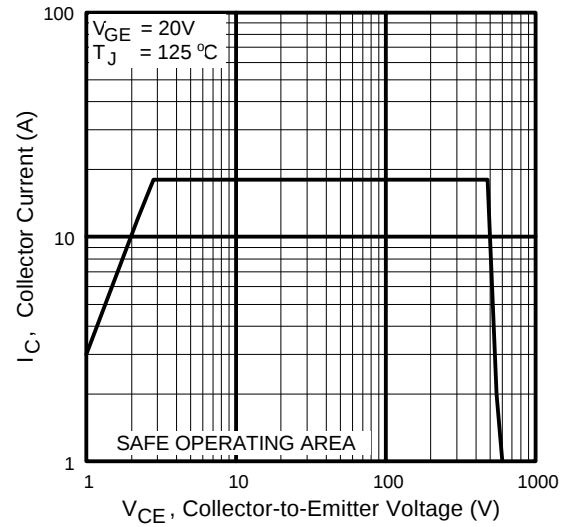
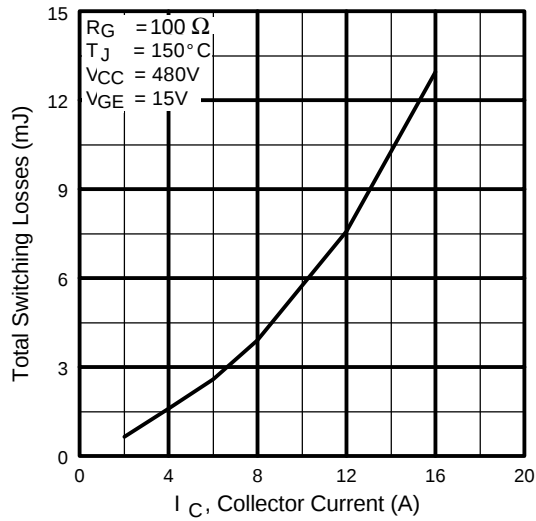


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

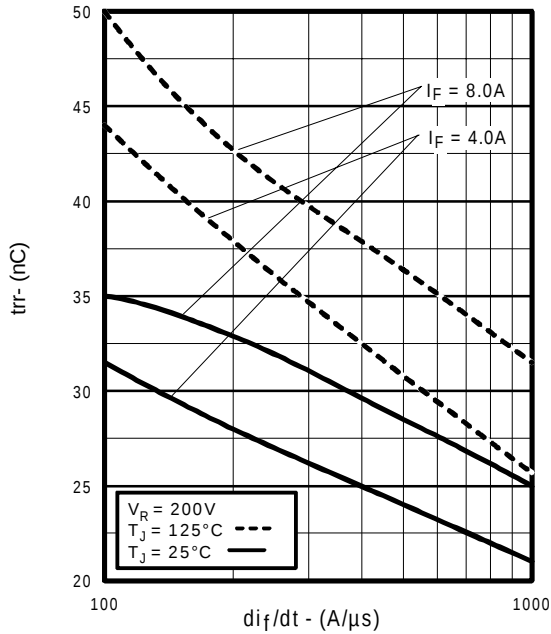


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

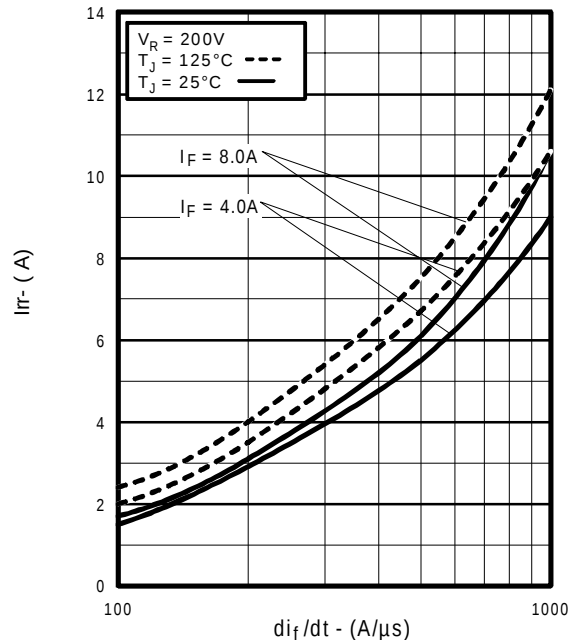


Fig. 15 - Typical Recovery Current vs. di_f/dt

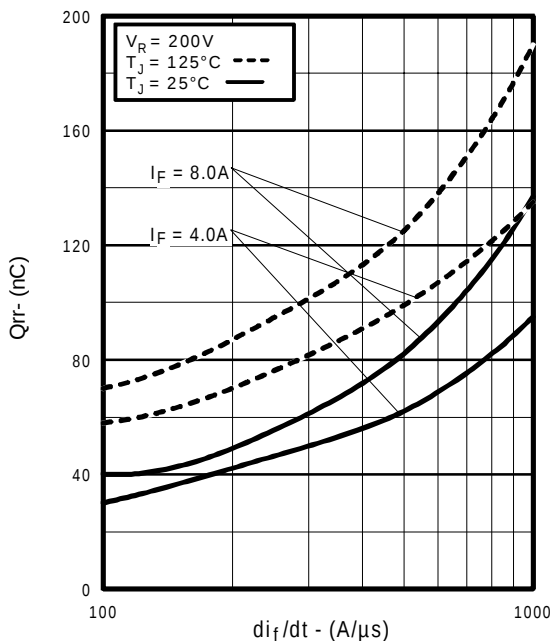


Fig. 16 - Typical Stored Charge vs. di_f/dt

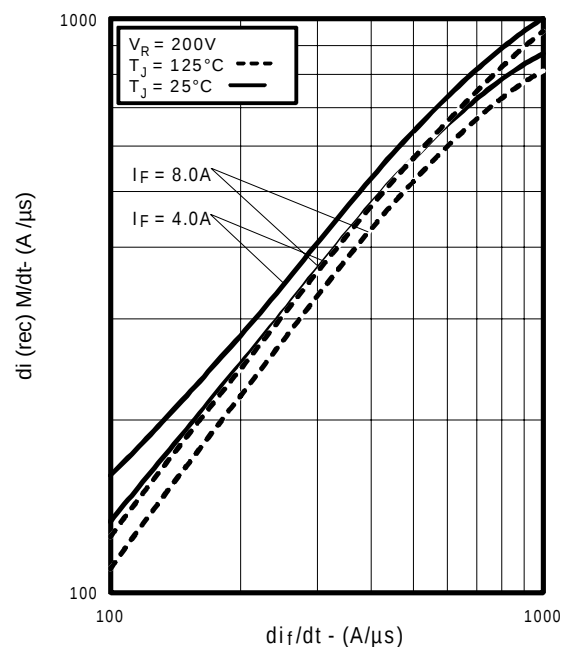


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

IRG4RC10SD

International
IR Rectifier

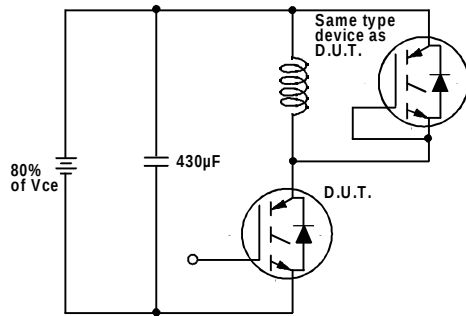


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

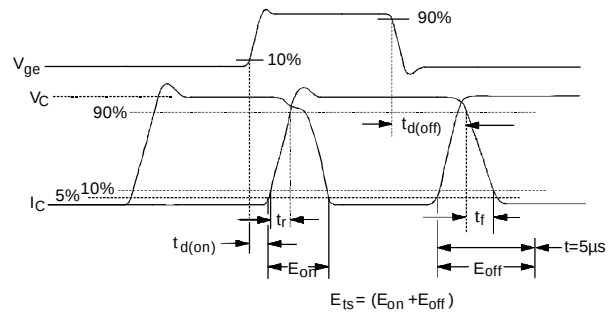


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

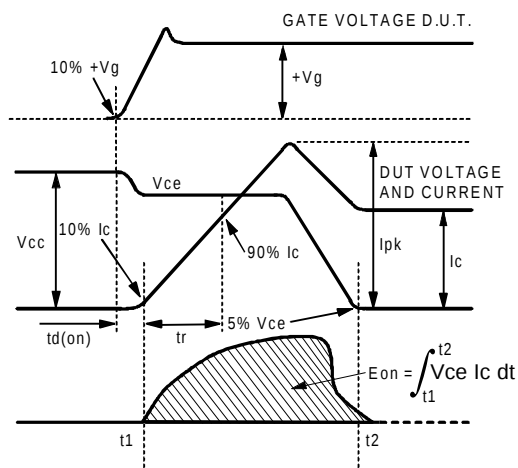


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

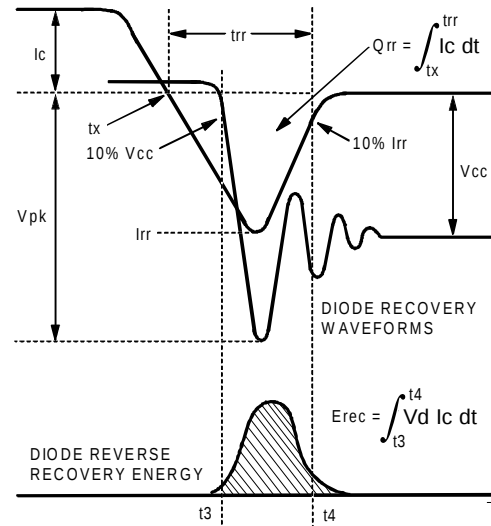


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

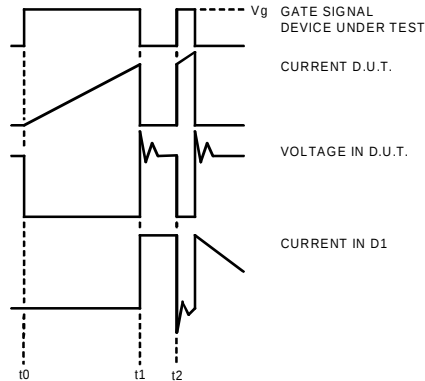


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

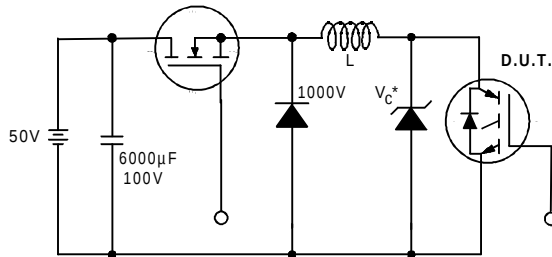


Figure 19. Clamped Inductive Load Test Circuit

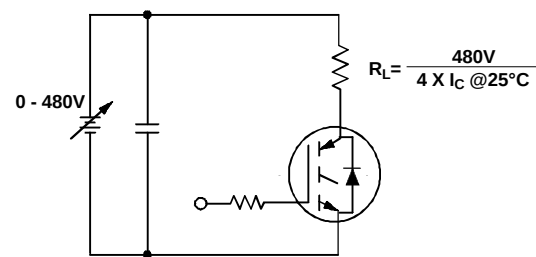
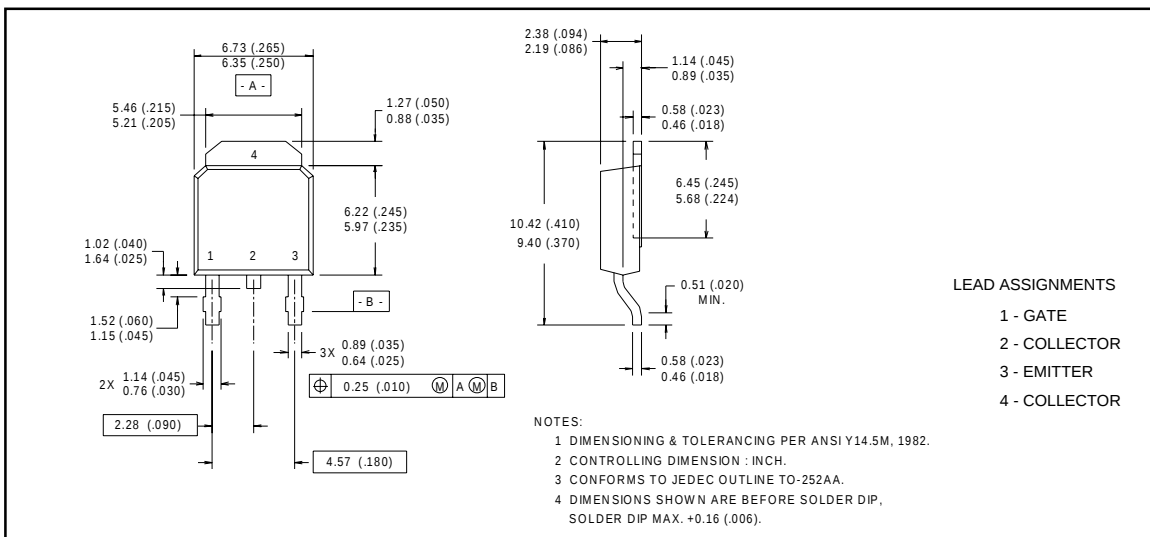


Figure 20. Pulsed Collector Current Test Circuit

Package Outline

TO-252AA Outline

Dimensions are shown in millimeters (inches)



IRG4RC10SD

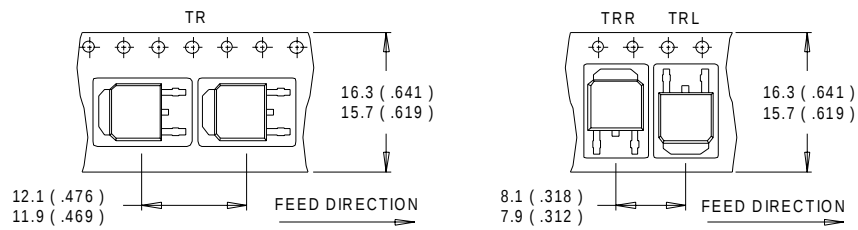
International
IR Rectifier

Notes:

- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G = 100W$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width $5.0\mu s$, single shot.

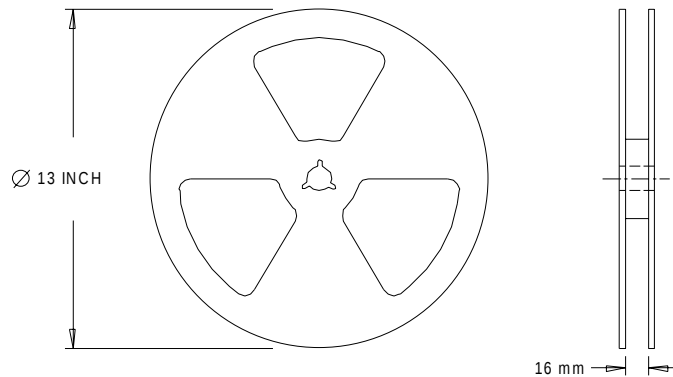
Tape & Reel Information

TO-252AA



NOTES :

- 1. CONTROLLING DIMENSION : MILLIMETER.
- 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
- 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

- 1. OUTLINE CONFORMS TO EIA-481.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105

TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.

Data and specifications subject to change without notice. 12/00